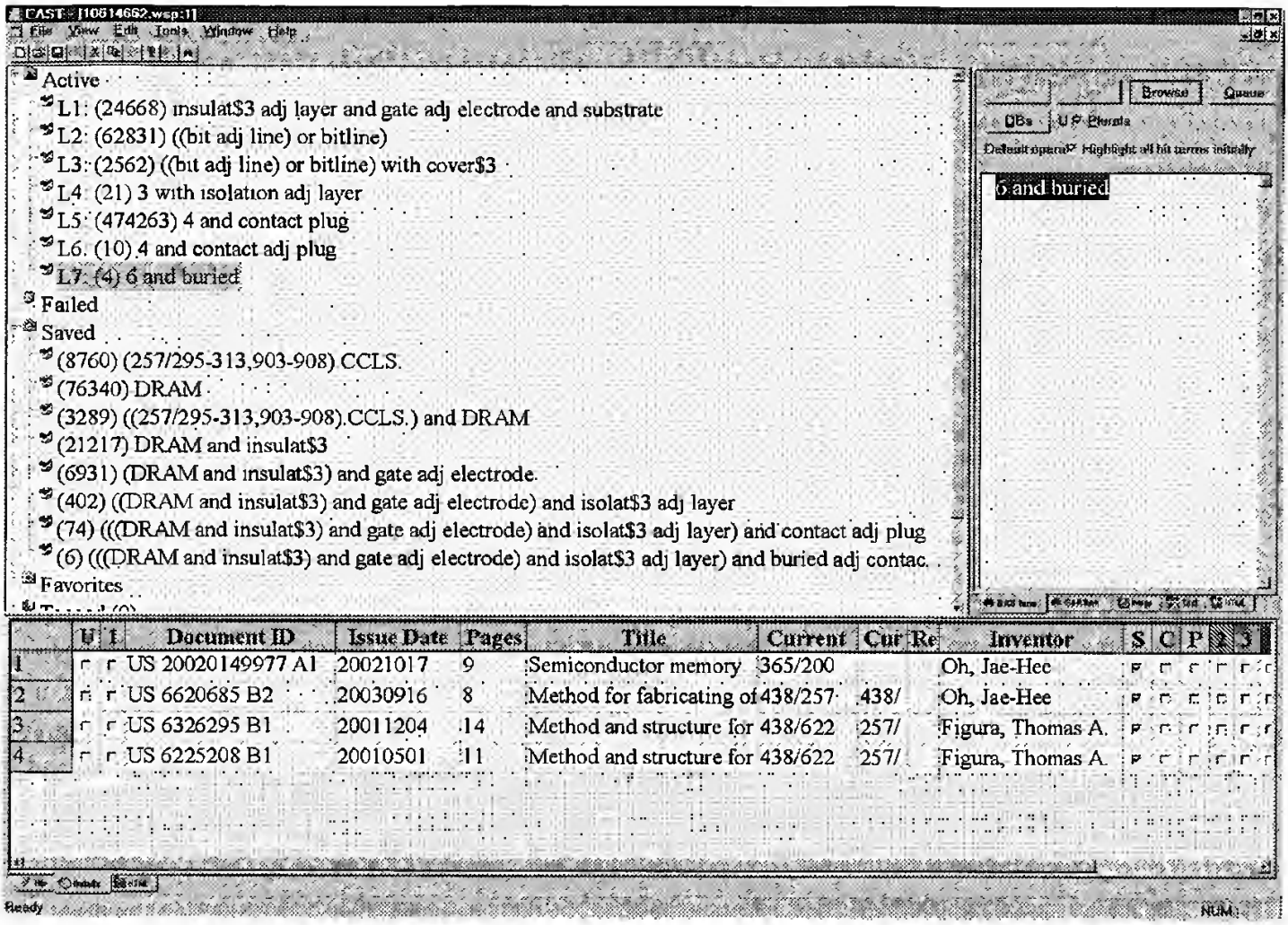

	U	I	Document ID	Issue Date	Pages	Title	Current	Cur Re	Inventor	S	C	P	2	3
1			US 20020149977 A1	20021017	9	Semiconductor memory	365/200		Oh, Jae-Hee					
2			US 6620685 B2	20030916	8	Method for fabricating of	438/257	438/	Oh, Jae-Hee					
3			US 6326295 B1	20011204	14	Method and structure for	438/622	257/	Figura, Thomas A.					
4			US 6225208 B1	20010501	11	Method and structure for	438/622	257/	Figura, Thomas A.					

L Number	Hits	Search Text	DB	Time stamp
1	24668	insulat$3 adj layer and gate adj electrode and substrate	USPAT; US-PGPUB, EPO; JPO, DERWENT, IBM_TDB	2003/12/05 09:25
2	62831	((bit adj line) or bitline)	USPAT, US-PGPUB; EPO; JPO, DERWENT; IBM_TDB	2003/12/05 09:26
3	2562	((bit adj line) or bitline) with cover$3	USPAT; US-PGPUB, EPO; JPO, DERWENT; IBM_TDB	2003/12/05 09:26
4	21	(((bit adj line) or bitline) with cover$3) with isolation adj layer	USPAT; US-PGPUB, EPO, JPO, DERWENT; IBM_TDB	2003/12/05 09:26
5	474263	((((bit adj line) or bitline) with cover$3) with isolation adj layer) and contact plug	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/05 09:27
6	10	((((bit adj line) or bitline) with cover$3) with isolation adj layer) and contact adj plug	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/12/05 09:27
7	4	(((((bit adj line) or bitline) with cover$3) with isolation adj layer) and contact adj plug) and buried	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/12/05 09:27
-	8760	(257/295-313,903-908).CCLS.	USPAT; US-PGPUB, EPO; JPO; DERWENT; IBM_TDB	2003/12/04 16:13
-	76340	DRAM	USPAT, US-PGPUB, EPO; JPO, DERWENT; IBM_TDB	2003/12/04 16:13
-	3289	((257/295-313,903-908) CCLS.) and DRAM	USPAT, US-PGPUB; EPO; JPO, DERWENT; IBM_TDB	2003/12/04 16:13
-	21217	DRAM and insulat$3	USPAT, US-PGPUB, EPO; JPO; DERWENT; IBM_TDB	2003/12/05 09:24
-	6931	(DRAM and insulat$3) and gate adj electrode	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/12/04 16:15

-	402	((DRAM and insulat$3) and gate adj electrode) and isolat$3 adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 16:16
-	74	(((DRAM and insulat$3) and gate adj electrode) and isolat$3 adj layer) and contact adj plug	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 16:16
-	6	(((DRAM and insulat$3) and gate adj electrode) and isolat$3 adj layer) and buried adj contact adj plug	USPAT; US-PGPUB; EPO; JPO, DERWENT; IBM_TDB	2003/12/04 16:16